

Top Hat profiles improve solar cell processing

Advantages

Process and quality improvement in various solar cell processing techniques:

- Direct Laser structuring raises the efficiency in structuring of solar cell and thin film panels
- Laser edge isolation to achieve high opto-electrical efficiency
- Laser fired contacts for a higher electron mobility
- Metal Wrap Through (MWT)

Safe and economical laser processing with:

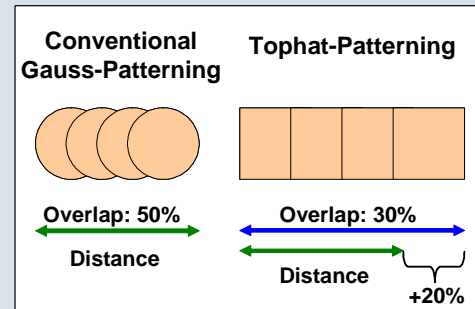
- No sawtooth pattern, which reduces the fracture of solar cells and the electrical break through
- High throughput
- For use with all kinds of single mode lasers

Innovative and reproducible micro structuring (maskless) of holes, contacts and grooves with:

- Safe removal of thin films due to a homogeneous profile without intensity spikes
- Groove widths down to 50 μm
- Straighter grooves compared to conventional structuring techniques
- Steep edges (no v-grooves)

Structuring of a broad range of materials including:

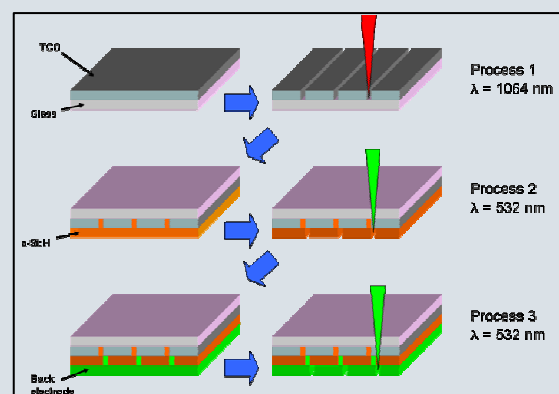
- Ceramics (SiO_2 , SiN , SiC ; TiO_2)
- Metals (Aluminium, CIS, CdTe, GaAs)
- Oxides (TCO), organic thin films



Advantage for Top-Hat patterning: **+20% faster in processes**



Left: Gaussian Grooves in TCO-Layer. Right: Top-Hat Grooves in TCO-Layer. Laser: Nd:YAG, SHG @532nm, 4W, 500kHz, 10ps-pulses



P1, P2 and P3 process for thin film solar cells (structure width < 100 μm)

Solution for your application

Gauss-to-Top-Hat-Converter Series 410.000

Performance

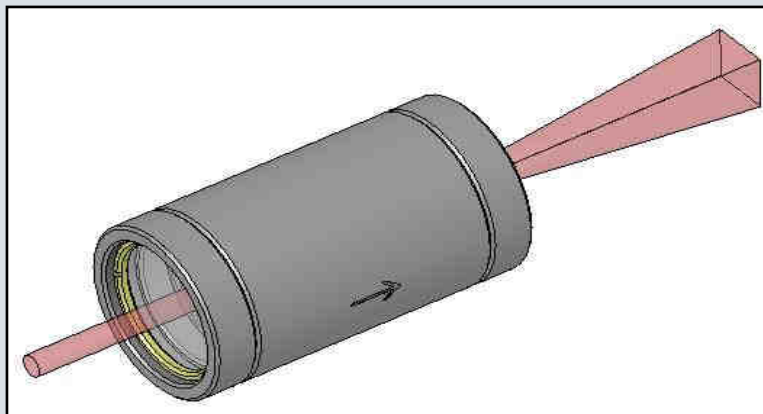
- Various field-shapes possible (squares, rectangles, lines)
- Output field-sizes from $50 \times 50 \mu\text{m}^2$ up to $10 \times 10 \text{mm}^2$
- Working distances between 50 – 500 mm
- Deep depth of focus
- Improved homogeneity up to 95 %
- Transmission > 97% (355, 532, 1064 nm)
- Robust and compact design (diameter = 31.5 mm; length = 58 mm)



Compact Gauss-to-Top-Hat-Converter Series 410.000

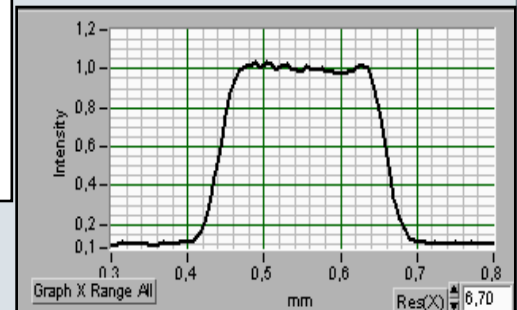
Easy integration into your system

The module has a solid industrial design, the Gauss-to-Top-Hat lenses are compact mounted and the module can be easily integrated in the beam path of the collimated laser beam.



This **Gauss-to-Top-Hat-Converter** produces a Top Hat beam profile by point-to-point mapping of the Gaussian input rays to relocate the intensity to a light line or rectangular field.

Typical beam profile (generated from a green laser @ 532 nm and a Gaussian input profile with $M^2 < 1.1$, 96% TEM_{00} mode)



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